Band Gap Engineering of MnO$_2$ through In-situ Al-doping for Applicable Pseudocapacitors

Tianqi Li, 1# Jiabin Wu, 2# Xu Xiao, 1 Bingyan Zhang, 1 Zhimi Hu, 1 Jun Zhou, 1 Peihua Yang, 1 Xun Chen, 1 Bo Wang, 1 Liang Huang 1*

1, Wuhan National Laboratory for Optoelectronics, School of Optical and Electronic Information, Huazhong University of Science and Technology, Wuhan 430074, P. R. China

2, School of Materials Science and Engineering, Wuhan University of Technology, Wuhan 430074, P. R. China.

#Authors with equal contribution.

Fig. S1. N2 adsorption-desorption isotherms of ASM and ADM.
Fig. S2. SEM and TEM image of ASM, which shows same morphology of ADM.

Fig. S3. CV curves of ASM from 2 mV s\(^{-1}\) to 200 mV s\(^{-1}\).
**Fig. S4.** The cycle testing of ADM and ASM through galvanostatic charge/discharge at 2 Ag⁻¹.

**Fig. S5.** UV-visible \((ahv)^{1/2}\) vs Ep curves for samples with different Al³⁺ concentration.